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Tọ:	Allan	Olsen	From:	Gregory Muir	
Fax:	703-8	72-9306	Pages:	7	
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We are in receipt of the Notice of Allowance and in reviewing the file we noticed that we have not received back the Information Disclosure Statement PTO 1449 forms that we filed on October 7, 2004. Attached please find the forms. Please sign and send back to us.

Thanks so much!

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Sheet	1	of	6	Attorney Docket Number	P68-US

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Complete if Known Substitute for form 1449A/PTO **Application Number** 09/954,864 **INFORMATION DISCLOSURE** 9/17/01 Filing Date STATEMENT BY APPLICANT First Named Inventor Patel Art Unit 1763 (use as many sheets as necessary) Examiner Name Olsen, Allan 3 of Sheet Attorney Docket Number P68-US

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Sheet	4	of	6	Attorney Docket Number	P68-US

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Examiner Initials	Cite No.1	Include name of the author (in CAPITAL LETTERS), tille of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(a), volume-issue number(s), oublisher, city and/or country where published.
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4		OTHER PRIOR ART NON PATENT LITERATURE DOCUMENTS	
Exeminer Iniliais	Cite No. 1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, sarial, symposium, catalog, etc.), date, page(s), volume-issue number(s), rebilisher, city and/or country where published.	
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